

Kibog Park

List of Publications by Year in descending order

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52
papers

1,196
citations

430874

18
h-index

377865

34
g-index

54
all docs

54
docs citations

54
times ranked

2319
citing authors

#	ARTICLE	IF	CITATIONS
1	C ₆₀ Adsorbed on TiO ₂ Drives Dark Generation of Hydroxyl Radicals. ACS Catalysis, 2022, 12, 5990-5996.	11.2	5
2	Self-selective ferroelectric memory realized with semimetallic graphene channel. Npj 2D Materials and Applications, 2021, 5, .	7.9	4
3	Capacitive Heart-Rate Sensing on Touch Screen Panel with Laterally Interspaced Electrodes. Sensors, 2020, 20, 3986.	3.8	5
4	Low-Cost and Fast-Response Resistive Humidity Sensor Comprising Biopolymer-Derived Carbon Thin Film and Carbon Microelectrodes. Journal of the Electrochemical Society, 2020, 167, 147511.	2.9	7
5	Edge-over MOSFET with poly-Si thin film channel for achieving thermodynamic limit of subthreshold swing in nanometer scale. Semiconductor Science and Technology, 2019, 34, 095014.	2.0	0
6	Multi-Level Capacitive Memory Effect in Metal/Oxide/Floating-Schottky Junction. Journal of the Korean Physical Society, 2019, 74, 979-983.	0.7	1
7	Reduction of water-molecule-induced current-voltage hysteresis in graphene field effect transistor with semi-dry transfer using flexible supporter. Journal of Applied Physics, 2019, 125, .	2.5	12
8	Negative Fermi-Level Pinning Effect of Metal/n-GaAs(001) Junction Induced by a Graphene Interlayer. ACS Applied Materials & Interfaces, 2019, 11, 47182-47189.	8.0	11
9	Formation of graphene on amorphous SiC film by surface-confined heating with electron beam irradiation. Current Applied Physics, 2018, 18, 335-339.	2.4	2
10	Surface-induced transition of nematic liquid crystals on graphene/SiC substrate. Europhysics Letters, 2018, 124, 46004.	2.0	1
11	One-Dimensional Assembly on Two-Dimensions: AuCN Nanowire Epitaxy on Graphene for Hybrid Phototransistors. Nano Letters, 2018, 18, 6214-6221.	9.1	30
12	Unveiling the Direct Correlation between the CVD-Grown Graphene and the Growth Template. Journal of Nanomaterials, 2018, 2018, 1-6.	2.7	4
13	Optical and microstructural properties of InGaN/GaN multiple quantum wells with embedded graphene coating. Journal of Alloys and Compounds, 2017, 713, 87-94.	5.5	0
14	Strong Fermi-Level Pinning at Metal/n-Si(001) Interface Ensured by Forming an Intact Schottky Contact with a Graphene Insertion Layer. Nano Letters, 2017, 17, 44-49.	9.1	26
15	Growth and Simultaneous Valleys Manipulation of Two-Dimensional MoSe ₂ -WSe ₂ Lateral Heterostructure. ACS Nano, 2017, 11, 8822-8829.	14.6	54
16	Stretchable Dual-Capacitor Multi-Sensor for Touch-Curvature-Pressure-Strain Sensing. Scientific Reports, 2017, 7, 10854.	3.3	37
17	Growth and characterization of $\hat{\Gamma}^2$ -Ga ₂ O ₃ thin films by molecular beam epitaxy for deep-UV photodetectors. Journal of Applied Physics, 2017, 122, .	2.5	124
18	Research on flexible display at Ulsan National Institute of Science and Technology. Npj Flexible Electronics, 2017, 1, .	10.7	59

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19	Highly-Sensitive Thin Film THz Detector Based on Edge Metal-Semiconductor-Metal Junction. Scientific Reports, 2017, 7, 16830.	3.3	7
20	On-Display Transparent Half-Diamond Pattern Capacitive Fingerprint Sensor Compatible With AMOLED Display. IEEE Sensors Journal, 2016, 16, 8124-8131.	4.7	35
21	Giant Electroresistance in Edge Metal-Insulator-Metal Tunnel Junctions Induced by Ferroelectric Fringe Fields. Scientific Reports, 2016, 6, 30646.	3.3	6
22	High-Performance Plasmonic THz Detector Based on Asymmetric FET With Vertically Integrated Antenna in CMOS Technology. IEEE Transactions on Electron Devices, 2016, 63, 1742-1748.	3.0	41
23	Schottky barrier modulation of metal/4H-SiC junction with thin interface spacer driven by surface polarization charge on 4H-SiC substrate. Applied Physics Letters, 2015, 107, .	3.3	17
24	Controllable Synthesis of Graphene-Encapsulated Low-Dimensional Nanocomposites. Advanced Materials Interfaces, 2015, 2, 1500112.	3.7	3
25	Performance Enhancement of Plasmonic Sub-Terahertz Detector Based on Antenna Integrated Low-Impedance Silicon MOSFET. IEEE Electron Device Letters, 2015, 36, 220-222.	3.9	23
26	Enhanced Crystallinity of Epitaxial Graphene Grown on Hexagonal SiC Surface with Molybdenum Plate Capping. Scientific Reports, 2015, 5, 9615.	3.3	7
27	Growth of Wrinkle-Free Graphene on Texture-Controlled Platinum Films and Thermal-Assisted Transfer of Large-Scale Patterned Graphene. ACS Nano, 2015, 9, 679-686.	14.6	52
28	Highly Flexible Touch Screen Panel Fabricated with Silver Nanowire Crossing Electrodes and Transparent Bridges. Journal of the Optical Society of Korea, 2015, 19, 508-513.	0.6	11
29	Ferroelectric enhancement of La-doped BaTiO ₃ thin films using SrTiO ₃ buffer layer. Thin Solid Films, 2014, 551, 127-130.	1.8	19
30	Photoresponse enhancement of plasmonic terahertz wave detector based on asymmetric silicon MOSFETs with antenna integration. Japanese Journal of Applied Physics, 2014, 53, 04EJ05.	1.5	14
31	Negative Poisson's ratios in metal nanoplates. Nature Communications, 2014, 5, 3255.	12.8	112
32	Monolithic graphene oxide sheets with controllable composition. Nature Communications, 2014, 5, 3383.	12.8	31
33	In situ observations of gas phase dynamics during graphene growth using solid-state carbon sources. Physical Chemistry Chemical Physics, 2013, 15, 10446.	2.8	21
34	TCAD modeling and simulation of non-resonant plasmonic THz detector based on asymmetric silicon MOSFETs. , 2013, , .		3
35	Low-temperature formation of epitaxial graphene on 6H-SiC induced by continuous electron beam irradiation. Applied Physics Letters, 2012, 101, 092105.	3.3	11
36	Terahertz antenna compatible with CMOS array detector for a real-time T-ray imaging system. , 2012, , .		1

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37	Facile Synthesis of Few-Layer Graphene with a Controllable Thickness Using Rapid Thermal Annealing. ACS Applied Materials & Interfaces, 2012, 4, 1777-1782.	8.0	28
38	Design and Characterization of Plasmonic Terahertz Wave Detectors Based on Silicon Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 06FE17.	1.5	9
39	One-step graphene coating of heteroepitaxial GaN films. Nanotechnology, 2012, 23, 435603.	2.6	33
40	Near room-temperature synthesis of transfer-free graphene films. Nature Communications, 2012, 3, 645.	12.8	205
41	Logarithmic temperature variations of the elastic constant of barium titanate near the ferroelectric phase transition. Current Applied Physics, 2012, 12, 1185-1189.	2.4	18
42	Ferroelectric phase transitions studied by dielectric and light scattering spectroscopies on Ba _{1-x} CaTiO ₃ single crystals (x= 0.12, 0.20). Ceramics International, 2012, 38, S21-S24.	4.8	4
43	Dependence of spontaneous polarization on stacking sequence in SiC revealed by local Schottky barrier height variations over a partially formed 8H-SiC layer on a 4H-SiC substrate. Applied Physics Letters, 2011, 99, .	3.3	3
44	Effect of Ca Content on the Acoustic Anomalies of Ba _{1-x} Ca _x TiO ₃ Single Crystals Studied by Brillouin Light Scattering. Journal of the Korean Physical Society, 2011, 59, 2575-2578.	0.7	2
45	Precursor polar clusters in the paraelectric phase of ferroelectric Ba _{0.80} Ca _{0.20} TiO ₃ single crystals studied by Brillouin light scattering. Journal of Physics Condensed Matter, 2010, 22, 225904.	1.8	12
46	Nanometer-resolution measurement and modeling of lateral variations of the effective work function at the bilayer Pt/Al. Physical Review B, 2009, 80, .	3.2	4
47	Valence band structure and band offset of 3C- and 4H-SiC studied by ballistic hole emission microscopy. Applied Physics Letters, 2006, 89, 042103.	3.3	10
48	Effect of inclined quantum wells on macroscopic capacitance-voltage response of Schottky contacts: Cubic inclusions in hexagonal SiC. Applied Physics Letters, 2005, 86, 222109.	3.3	15
49	Quantum well behavior of single stacking fault 3C inclusions in 4H-SiC p-i-n diodes studied by ballistic electron emission microscopy. Applied Physics Letters, 2005, 87, 232103.	3.3	15
50	Cubic inclusions in 4H-SiC studied with ballistic electron-emission microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1351-1355.	2.1	2
51	Quantum well state of self-forming 3C SiC inclusions in 4H-SiC determined by ballistic electron emission microscopy. Physical Review B, 2004, 69, .	3.2	30
52	Simulations of denuded-zone formation during growth on surfaces with anisotropic diffusion. Physical Review B, 2003, 68, .	3.2	8